

KP 1000 - * *

ZP General Purpose Rectifiers
KP Phase Control Thyristors
ZK Fast Recovery Rectifiers
KK Fast Switching Thyristors
KS Triacs
ZW Welding Diodes

Rated Voltage Class ($** \times 100 = V_{DRM}/V_{RRM}$)

Rated Current $I_{T(AV)}/I_{F(AV)}$

TT 200 - * *

TT: Dual Thyristors
TD: Thyristor with Diode
DT: Diode with Thyristor
DD: Dual Diodes
TZ: Single Thyristor
DZ: Single Diode

Rated Voltage Class ($** \times 100 = V_{DRM}/V_{RRM}$)

Rated Current $I_{T(AV)}/I_{F(AV)}$

M T C 90 - * *

Module

D:General Purpose Rectifiers
T: Phase Control Thyristors
Z: Fast Recovery Rectifiers
K: Fast Switching Thyristors
F: D&T
H: Z&K

Rated Voltage Class ($** \times 100 = V_{DRM}/V_{RRM}$)

Rated Current $I_{T(AV)}/I_{F(AV)}$

C: Series
K: Common Cathode
A: Common Anode
Y: Three Phase Common Cathode
G: Three Phase Common Anode
X: Anti-parallel
Q: Single Phase Bridge
S: Three Phase Bridge

Product	Parameter symbol	参数名称	Parameter Name
Rectifier Diode	V_{RRM}	反向重复峰值电压	Repetitive peak reverse voltage
	V_{FM}	正向峰值电压	Peak forward voltage
	$V_{F(AV)}$	正向平均电压	Mean forward voltage
	V_{FO}	门槛电压	Threshold voltage
	$I_{F(RSM)}$	正向方均根电流	Rms forward current
	$I_{F(AV)}$	正向平均电流	Mean forward current
	I_{FMS}	浪涌电流	Surge forward current
	I_{RRM}	反向重复峰值电流	Repetitive peak reverse current
	$I_{RR(AV)}$	反向重复平均电流	Repetitive mean reverse current
	I^2t	I^2t	I^2t
	T_j	工作结温	Operating junction temperature
	T_{stg}	贮存温度	Storage temperature
	Q_{rr}	恢复电荷	Recovery time
	t_{rr}	反向恢复时间	Reverse recovery time
	R_{jc}	结壳热阻	Thermal resistance junction-case
	r_{FO}	正向斜率电阻	Forward slope resistance
	I_{RRM}	反向重复峰值电流	Repetitive peak reverse current
	$I_{RR(AV)}$	反向重复平均电流	Repetitive mean reverse current
	I_{GT}	门极触发电流	Gate trigger current
	I_H	维持电流	Holding current
	I_{GM}	门极峰值电流	Peak gate current
	I^2t	I^2t	I^2t
	P_{GM}	门极峰值功率	Peak gate power
	$P_{G(AV)}$	门极平均功率	Mean gate power
	T_j	工作结温	Operating junction temperature
Phase Control Thyristor	t_{gt}	门极控制开通时间	Gate-controlled turn-on time
	t_q	电路换向关断时间	Circuit-commutated turn-off time
	dv/dt	断态电压临界上升率	Critical rate of rise of off-state voltage
	r_{TO}	通态斜率电阻	On-state slope resistance
	T_{stg}	贮存温度	Storage temperature
	V_{RRM}	反向重复峰值电压	Repetitive peak reverse voltage
	V_{DRM}	断态重复峰值电压	Repetitive peak off-state voltage
	V_{RGM}	门极反向峰值电压	Peak reverse gate voltage
	V_{TM}	通态峰值电压	Peak on-state voltage
	$V_{T(AV)}$	通态平均电压	Mean on-stage voltage
	V_{GT}	门极触发电压	Gate trigger voltage
	V_{GD}	门极不触发电压	Gate non-trigger voltage
	V_{TO}	通态门槛电压	On-state threshold voltage
	V_{GM}	门极峰值电压	Peak gate voltage
	$V_{T(RMS)}$	通态方均根电压	R.M.S on-state voltage
	$I_{T(AV)}$	通态平均电流	Mean on-state current
	$I_{T(RMS)}$	通态方均根电流	R.M.S on-state current
	I_{FGM}	门极正向峰值电流	Forward gate current
	I_{DRM}	断态重复峰值电流	Repetitive peak off-state current
	$I_{DR(AV)}$	断态重复平均电流	Repetitive mean off-state current
	I_{TSM}	浪涌电流	Surge on-state current